TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT process)

2SA1225

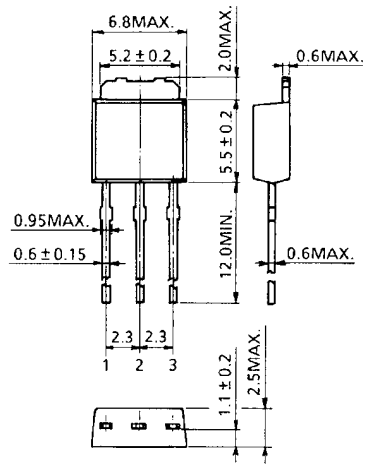
Power Amplifier Applications
Driver Stage Amplifier Applications

- High transition frequency: f_T = 100 MHz (typ.)
- Complementary to 2SC2983

Maximum Ratings (Ta = 25°C)

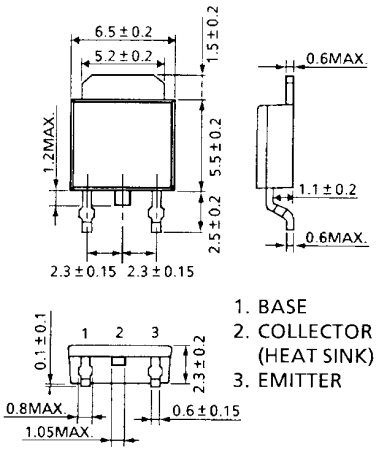
Characteristics		Symbol	Rating	Unit
Collector-base voltage		V_{CBO}	−160	V
Collector-emitter voltage		V_{CEO}	−160	V
Emitter-base voltage		V_{EBO}	−5	V
Collector current		I_C	−1.5	A
Base current		I_B	−0.3	A
Collector power dissipation	Ta = 25°C	P_C	1.0	W
	Tc = 25°C		15	
Junction temperature		T_j	150	°C
Storage temperature range		T_{stg}	−55 to 150	°C

Unit: mm



JEDEC	—
JEITA	—
TOSHIBA	2-7B1A

Weight: 0.36 g (typ.)



JEDEC	—
JEITA	—
TOSHIBA	2-7J1A

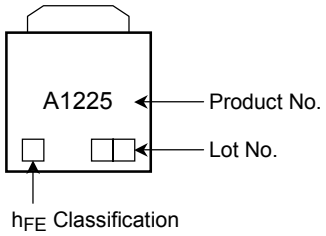
Weight: 0.36 g (typ.)

Electrical Characteristics (Ta = 25°C)

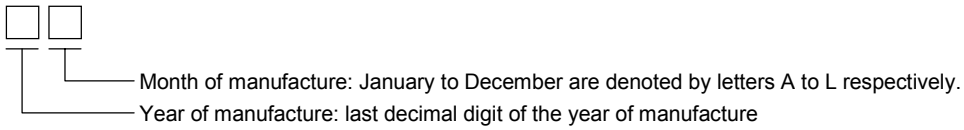
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	V_{CB} = −160 V, I_E = 0	—	—	−1.0	μA
Emitter cut-off current	I_{EBO}	V_{EB} = −5 V, I_C = 0	—	—	−1.0	μA
Collector-emitter breakdown voltage	$V_{(BR)\ CEO}$	I_C = −10 mA, I_B = 0	−160	—	—	V
Emitter-base breakdown voltage	$V_{(BR)\ EBO}$	I_E = −1 mA, I_C = 0	−5	—	—	V
DC current gain	h_{FE} (Note)	V_{CE} = −5 V, I_C = −100 mA	70	—	240	
Collector emitter saturation voltage	$V_{CE\ (sat)}$	I_C = −500 mA, I_B = −50 mA	—	—	−1.5	V
Base-emitter voltage	V_{BE}	V_{CE} = −5 V, I_C = −500 mA	—	—	−1.0	V
Transition frequency	f_T	V_{CE} = −10 V, I_C = −100 mA	—	100	—	MHz
Collector output capacitance	C_{ob}	V_{CB} = −10 V, I_E = 0, f = 1 MHz	—	30	—	pF

Note: h_{FE} classification O: 70 to 140, Y: 120 to 240

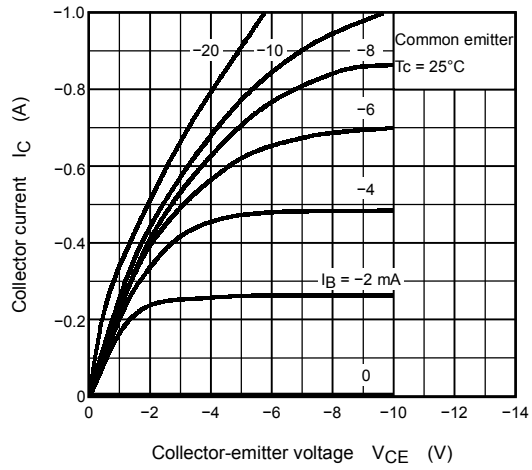
Marking



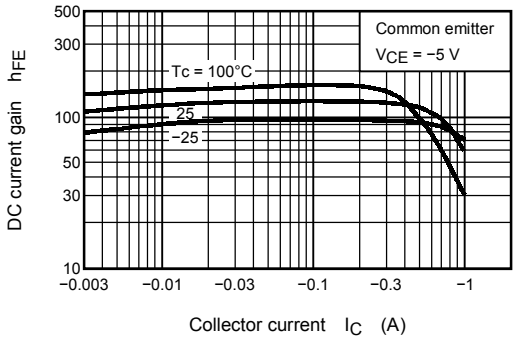
Explanation of Lot No.



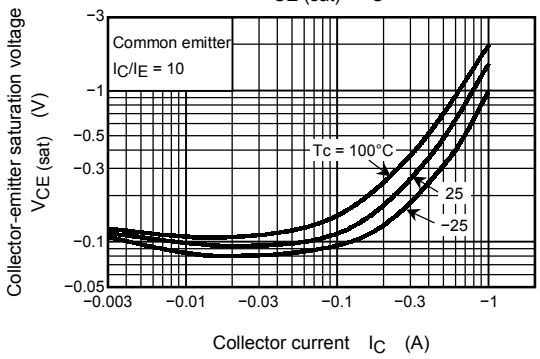
$I_C - V_{CE}$



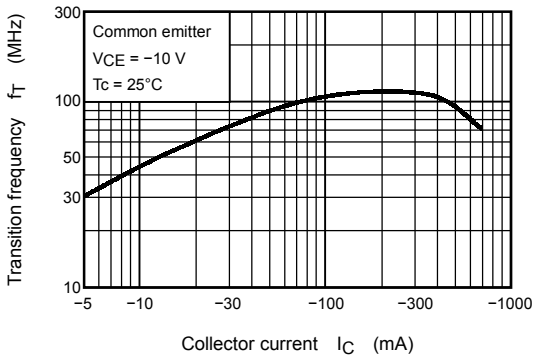
$h_{FE} - I_C$



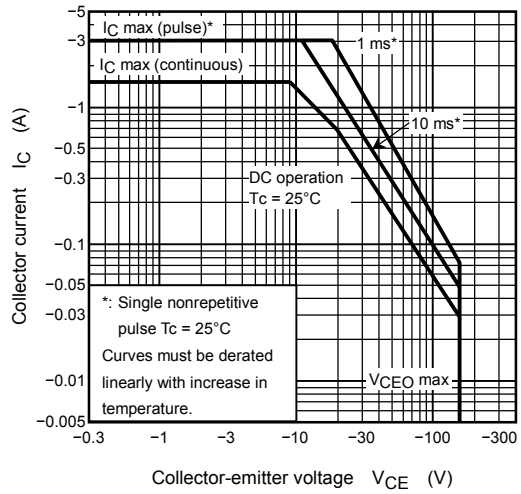
$V_{CE\ (sat)} - I_C$



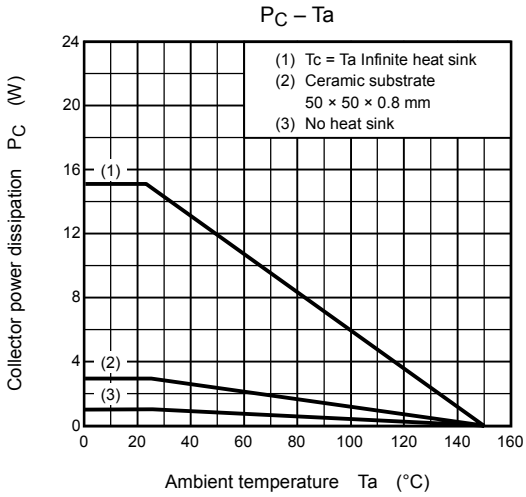
$f_T - I_C$



Safe Operating Area



$P_C - Ta$



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